

## **DETAILED ACTION**

### ***Examiner's Amendment***

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mr. Jurgen Vollrath on 9/23/2010.

The application has been amended as follows:

Please cancel claims 1, 3 and 4.

Claim 2, line 4, after "in the n-well", delete "to define an anode," and insert ---wherein the first n+ region defines a drain,---

Claim 2, line 6, after "in the p-well", delete "to define a cathode," and insert ---wherein the second n+ region defines a source,---

Claim 2, line 8, after "providing a gate" insert ---above a channel region, the channel region is located---

Claim 2, line 8, after "between the", delete "anode" and insert ---drain---

Claim 2, line 8, after "and the", delete "cathode" and insert ---source---

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Claim 2, line 10, after “inside the p-well of the”, insert ---LVTSCR---

Claim 2, line 12, after “second p+ region forming”, delete “a” and insert ---an anode---

Claim 2, line 12, after “the p-n junction”, insert ---of the diode---

Claim 2, line 14, after “region”, delete “of the p-n junction”

Claim 2, line 14, after “located”, delete “further” and insert ---at a first distance---

Claim 2, line 14, after “from the”, delete “high voltage node than” and insert ---drain and---

Claim 2, line 15, after “second p+ region”, delete “, wherein the diode is located between the anode and the cathode” and insert ---located at a second distance from the drain, wherein the first distance is greater than the second distance---

Claim 9, line 3, before “structure”, insert ---LVTSCR---

Claim 9, line 3, before “p-n junction”, insert ---forward biased---

Claim 9, line 3, after “p-n junction”, delete “in the p-well, each diode being formed by a p-type material and an n-type material, wherein the p-type material is defined by the p-well having one of the additional p+ regions or the second p+ region as diode contact, and wherein the n-type material is defined by one of the additional n+ regions” and insert ---under normal operation---

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ori Nadav whose telephone number is 571-272-1660. The examiner can normally be reached between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lynne Gurley can be reached on 571-272-1670. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

O.N.  
10/5/2010

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